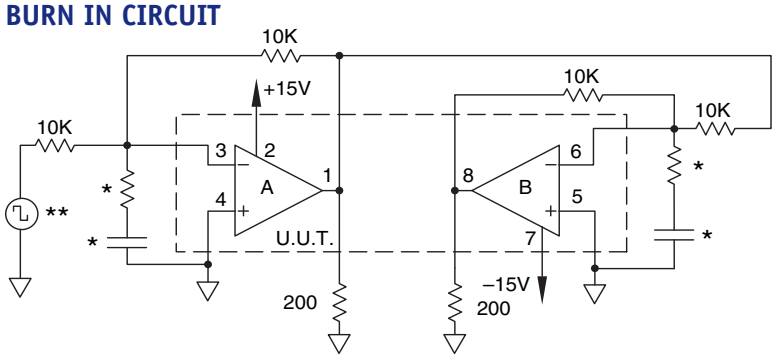
SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiesent Current	I_Q	25°C	±15	V_{IN} = 0, A_V = 100		30	mA
1	Input Offset Voltage	V_{OS}	25°C	±2.5	V_{IN} = 0, A_V = 100		10	mV
1	Input Offset Voltage	V_{OS}	25°C	±15	V_{IN} = 0, A_V = 100		10	mV
1	Input Offset Voltage	V_{OS}	25°C	±20	V_{IN} = 0, A_V = 100		14	mV
1	Input Bias Current + IN	$+I_B$	25°C	±15	V_{IN} = 0		1000	nA
1	Input Bias Current –IN	$-I_B$	25°C	±15	V_{IN} = 0		1000	nA
1	Input Offset Current	I_{OS}	25°C	±15	V_{IN} = 0		500	nA
3	Quiesent Current	I_Q	–55°C	±15	V_{IN} = 0, A_V = 100		30	mA
3	Input Offset Voltage	V_{OS}	–55°C	±2.5	V_{IN} = 0, A_V = 100		14	mV
3	Input Offset Voltage	V_{OS}	–55°C	±15	V_{IN} = 0, A_V = 100		14	mV
3	Input Offset Voltage	V_{OS}	–55°C	±20	V_{IN} = 0, A_V = 100		18	mV
3	Input Bias Current + IN	$+I_B$	–55°C	±15	V_{IN} = 0		1000	nA
3	Input Bias Current –IN	$-I_B$	–55°C	±15	V_{IN} = 0		1000	nA
3	Input Offset Current	I_{OS}	–55°C	±15	V_{IN} = 0		500	nA
2	Quiesent Current	I_Q	125°C	±15	V_{IN} = 0, A_V = 100		40	mA
2	Input Offset Voltage	V_{OS}	125°C	±2.5	V_{IN} = 0, A_V = 100		15	mV
2	Input Offset Voltage	V_{OS}	125°C	±15	V_{IN} = 0, A_V = 100		15	mV
2	Input Offset Voltage	V_{OS}	125°C	±20	V_{IN} = 0, A_V = 100		19	mV
2	Input Bias Current + IN	$+I_B$	125°C	±15	V_{IN} = 0		1000	nA
2	Input Bias Current –IN	$-I_B$	125°C	±15	V_{IN} = 0		1000	nA
2	Input Offset Current	I_{OS}	125°C	±15	V_{IN} = 0		500	nA
4	Output Voltage I_O= 2A	V_O	25°C	±9.5	R_L = 3Ω	6.0		V
4	Output Voltage I_O= 100mA	V_O	25°C	±11	R_L = 100Ω	9.9		V
4	Output Voltage I_O= 1A	V_O	25°C	±4.8	R_L = 3Ω	2.8		V
4	Stability/Noise	E_N	25°C	±15	R_L = 500Ω, A_V = 1 C_L = 1.5nF		1.0	mV
4	Crosstalk	XTLK	25°C	±15	R_L = 3Ω	50		dB
4	Slew Rate	SR	25°C	±15	R_L = 500Ω	.5		V/µS
4	Open Loop Gain	A_{OL}	25°C	±15	R_L = 500Ω, F =10Hz	75		dB
4	Common-mode Rejection	CMR	25°C	±17	R_L = 500Ω, V_{CM} = ±14V	60		dB
6	Output Voltage I_O= 2A	V_O	–55°C	±9.5	R_L = 3Ω	6.0		V
6	Output Voltage I_O= 100mA	V_O	–55°C	±11	R_L = 100Ω	9.9		V
6	Output Voltage I_O= 1A	V_O	–55°C	±4.8	R_L = 3Ω	2.8		V
6	Stability/Noise	E_N	–55°C	±15	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1.0	mV
6	Slew Rate	SR	–55°C	±15	R_L = 500Ω	.5		V/µS
6	Open Loop Gain	A_{OL}	–55°C	±15	R_L = 500Ω, F = 10Hz	75		dB
6	Common-mode Rejection	CMR	–55°C	±17	R_L = 500Ω, V_{CM} = ±14V	60		dB
5	Output Voltage I_O= 1A	V_O	125°C	±4.8	R_L = 3Ω	2.8		V
5	Output Voltage I_O= 100mA	V_O	125°C	±11	R_L = 100Ω	9.9		V
5	Output Voltage I_O= 750mA	V_O	125°C	±4.0	R_L = 3Ω	2.25		V
5	Stability/Noise	E_N	125°C	±15	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1.0	mV
5	Slew Rate	SR	125°C	±15	R_L = 500Ω	.5		V/µS
5	Open Loop Gain	A_{OL}	125°C	±15	R_L = 500Ω, F = 10Hz	75		dB
5	Common-mode Rejection	CMR	125°C	±17	R_L = 500Ω, V_{CM} = ±14V	60		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.

This data sheet has been carefully checked and is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. All specifications are subject to change without notice.